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ATTY DOCKET NO. D/98779i3

PLICATION NO.
09/277.328

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APPLICANT Michael A. Kneissl et al.

FILING DATE 3/26/1999

GROUP ART UNIT 2874

~~JUL 30 1990~~

U.S. PATENT DOCUMENTS





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FOREIGN PATENT DOCUMENTS

	COUNTRY	DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	TRANSLATION Y/N

OTHER DOCUMENTS (Including Author (in CAPS), Title, Publication Date, Pages, etc.)

	A. Kuramata, S. Kubota, R. Soejima, K. Domen, K. Horino and T. Tanahashi. "Room-Temperature Continuous Wave Operation of InGaN Laser Diodes with Vertical Conducting Structure on SiC Substrate". Japanese Journal of Applied Physics, Vol. 37, Part 2, No. 11B, 15 Novmeber 1998, pp. L1373-L1375. _____
	S. Nakamura, M. Senoh, S. Nagahama, N. Iwasa, T. Yamada, T. Matsushita, H. Kiyoku, Y. Sugimoto, T. Kozaki, H. Umemoto, M. Sano and K. Chocho. "Continuous-wave operation of InGaN/GaN/AlGaIn-based laser diodes grown on GaN substrates". <i>APPLIED PHYSICS LETTERS</i> , Vol. 72, No. 16, 10 April 1998, pp. 2014-2016.
	S. Nakamura, M. Senoh, S. Nagahama, N. Iwasa, T. Yamada, T. Matsushita, H. Kiyoku, Y. Sugimoto, T. Kozaki, H. Umemoto, M. Sano and K. Chocho. "InGaN/GaN/AlGaIn-based laser diodes with modulation-doped strained-layer superlattices grown on an epitaxially laterally overgrown GaN substrate". <i>APPLIED PHYSICS LETTERS</i> , Vol. 72, No. 2, 12 January 1998, pp. 211-213.
	S. Nakamura, G. Fasol. "The Blue Laser Diode. GaN Based Light Emitters and Lasers." <i>Springer</i> , 1997. pp. 34-47, 190-193 & 223-259.

EXAMINER

DATE CONSIDERED 3/1/0

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